

AM4457P3C-F-R

Phototransistor

DESCRIPTION

· Made with NPN silicon phototransistor chips

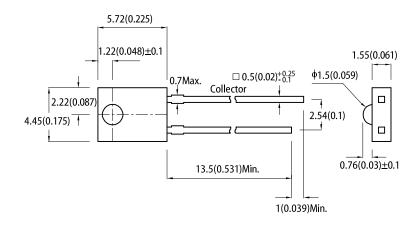
FEATURES

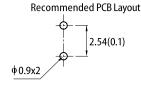
- · Mechanically and spectrally matched to infrared emitting LED lamp
- Halogen-free
- · Water clear lens
- RoHS compliant

APPLICATIONS

- · Infrared applied systems
- · Optoelectronic switches
- Photodetector control circuits
- · Sensor technology

PACKAGE DIMENSIONS





- All dimensions are in millimeters (inches).

- 2. Tolerance is ±0.25(0.01") unless otherwise noted.
 3. Lead spacing is measured where the leads emerge from the package.
 4. The specifications, characteristics and technical data described in the datasheet are subject to change

ABSOLUTE MAXIMUM RATINGS at T_A=25°C

Parameter	Max.Ratings	Units
Collector-to-Emitter Voltage	30	V
Emitter-to-Collector Voltage	5	V
Power Dissipation at (or below) 25°C Free Air Temperature	100	mW
Operating Temperature	-40 to +85	°C
Storage Temperature	-40 to +85	°C
Lead Soldering Temperature(>5mm for 5sec)	260	°C

Note:
1. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.



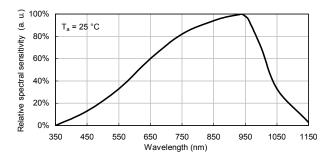


ELECTRICAL / OPTICAL CHARACTERISTICS at T_A=25°C

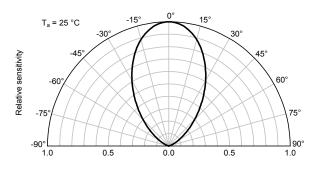
Parameter	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Collector-to-Emitter Breakdown Voltage	V _{BR CEO}	30	-	-	V	$I_C = 100\mu A$ $E_e = 0 mW/cm^2$
Emitter-to-Collector Breakdown Voltage	V _{BR ECO}	5	-	-	V	$I_E = 100\mu A$ $E_e = 0 \text{mW/cm}^2$
Collector-to-Emitter Saturation Voltage	V _{CE (SAT)}	-	-	0.8	V	$I_C = 2mA$ $E_e = 20mW/cm^2$
Collector Dark Current	I _{CEO}	-	-	100	nA	$V_{CE} = 10V$ $E_e = 0$ mW/cm ²
Rise Time(10% to 90%)	T _R	-	15	-	μS	$V_{CE} = 5V$ $I_{C} = 1mA$ $R_{L} = 1000\Omega$
Fall Time(90% to 10%)	T _F	-	15	-	μS	
On State Collector Current	I _(ON)	0.35	0.8	-	mA	$V_{CE} = 5V$ $E_e = 1 \text{mW/cm}^2$ $\lambda = 940 \text{nm}$
Range of spectral bandwidth	λ _{0.1}	420	-	1120	nm	-
Wavelength of peak sensitivity	λ_{p}	-	940	-	nm	-
Angle of half sensitivity	2θ1/2	-	70	-	deg	-

TECHNICAL DATA

RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH



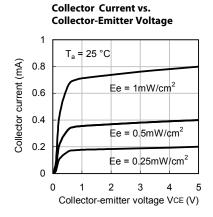
RELATIVE RADIANT SENSITIVITY vs. ANGULAR DISPLACEMENT

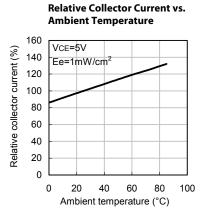


PHOTOTRANSISTOR

Irradiance 10 VCE=5V Collector current Ic (mA) T_a = 25 °C 0.1 0.01 0.01 0.1 10 Irradiance Ee (mW/cm²)

Collector Current vs.

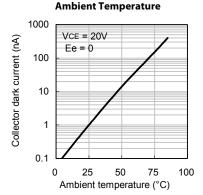






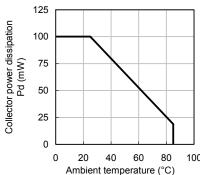
TECHNICAL DATA

Collector Dark Current vs.

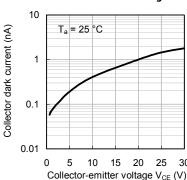


PHOTOTRANSISTOR

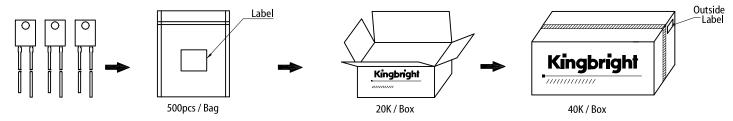
Collector Power Dissipation vs. **Ambient Temperature** 125 100

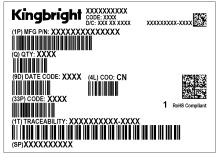


Collector Dark Current vs. **Collector-Emitter Voltage**



PACKING & LABEL SPECIFICATIONS





PRECAUTIONARY NOTES

- The information included in this document reflects representative usage scenarios and is intended for technical reference only.
- The part number, type, and specifications mentioned in this document are subject to future change and improvement without notice. Before production usage customer should refer to the latest datasheet for the updated specifications.
- When using the products referenced in this document, please make sure the product is being operated within the environmental and electrical limits specified in the datasheet. If customer usage exceeds the specified limits, Kingbright will not be responsible for any subsequent issues.

 The information in this document applies to typical usage in consumer electronics applications. If customer's application has special reliability requirements or have life-threatening
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